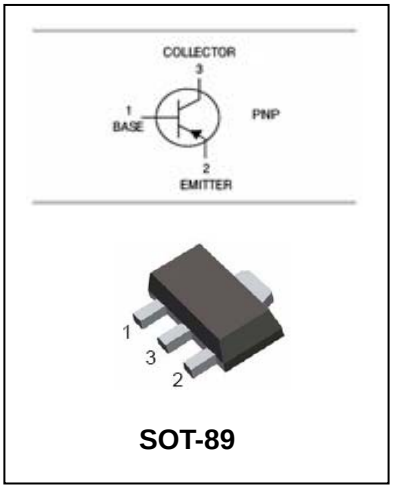
Silicon Planar Epitaxial Transistor 2SA1204

FEATURES

Lead-free

- Suitable for output stage of3 watts Amplifier
- Suitable flat package
- High DC current gain
- P_C=1.0 to 2.0W(mounted on ceramic substrate)
- Complementary to 2SC2884



SOT-89

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1204	RO/RY	SOT-89

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-35	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-800	mA
I_B	Base Current	-160	mA
P_C	Collector Dissipation	500 1000(Note)	mW
T_j,T_{stg}	Junction and Storage Temperature	-55~150	℃

Note1:Mounted on ceramic substrate(250mm^2*0.8t)

Silicon Planar Epitaxial Transistor 2SA1204

ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-30			V
Collector cut-off current	I_{CBO}	V_{CB}=-35V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-1V,I_C=-100mA	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA,I_B=-20mA			-0.7	V
Base-emitter	V_{BE}	V_{CE}=-1V,I_C=-10mA	-0.5		-0.8	V
Transition frequency	f_T	V_{CE}=-5V, I_C=-10mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		19		pF

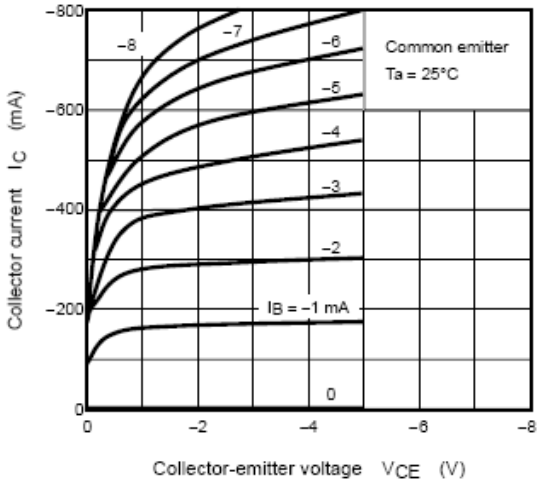
CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320
Marking	RO	RY

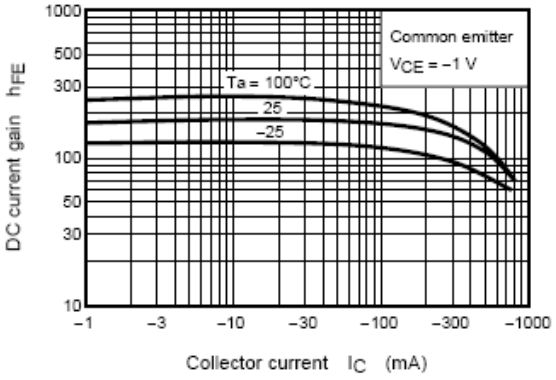
Silicon Planar Epitaxial Transistor 2SA1204

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

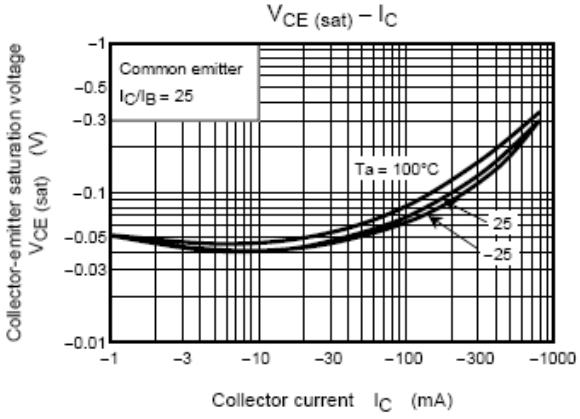
$I_C - V_{CE}$



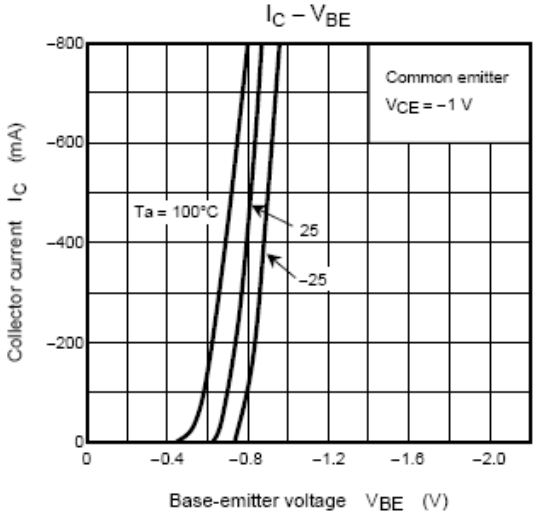
$h_{FE} - I_C$



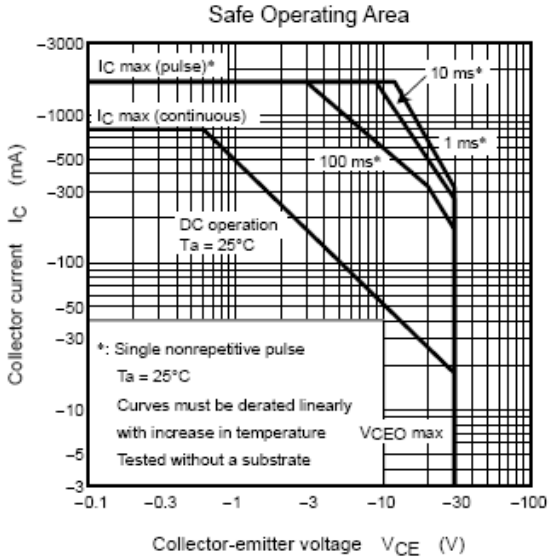
$V_{CE\ (sat)} - I_C$



$I_C - V_{BE}$



Safe Operating Area



$P_C - Ta$

